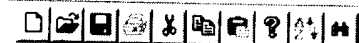


L Number	Hits	Search Text	DB	Time stamp
1	5	"6140688"	USPAT;	2002/08/01 08:51
2	923	((conduct\$3 metal) near3 layer) with work adj function	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM_TDB	2002/08/01 09:03
3	544	((((conduct\$3 metal) near3 layer) with work adj function) and ((first second) with (metal work conduct\$3)))	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM_TDB	2002/08/01 09:16
4	504	(((((conduct\$3 metal) near3 layer) with work adj function) and ((first second) with (metal work conduct\$3))) and (oxide 'TiN' titanium tantalum'Pt' 'Al' 'TaN'))	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM_TDB	2002/08/01 09:23
5	474	(((((conduct\$3 metal) near3 layer) with work adj function) and ((first second) with (metal work conduct\$3))) and (oxide 'TiN' titanium tantalum'Pt' 'Al' 'TaN')) and (thick thickness)	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM_TDB	2002/08/01 09:24
6	123	((((((conduct\$3 metal) near3 layer) with work adj function) and ((first second) with (metal work conduct\$3))) and (oxide 'TiN' titanium tantalum'Pt' 'Al' 'TaN')) and (thick thickness)) and ((thick thickness) with work adj function)	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM_TDB	2002/08/01 09:26
7	69	((((((conduct\$3 metal) near3 layer) with work adj function) and ((first second) with (metal work conduct\$3))) and (oxide 'TiN' titanium tantalum'Pt' 'Al' 'TaN')) and (thick thickness)) and ((thick thickness) with work adj function)) and (transistor gate)	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM_TDB	2002/08/01 09:33
8	69	((((((conduct\$3 metal) near3 layer) with work adj function) and ((first second) with (metal work conduct\$3))) and (oxide 'TiN' titanium tantalum'Pt' 'Al' 'TaN')) and (thick thickness)) and ((thick thickness) with work adj function)) and (transistor gate)) and work adj function	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM_TDB	2002/08/01 09:33



L1: (5) "6140688"

L2: (923) ((conduct\$3 metal) near3 layer) with work adj functio

L3: (544) 2 and ((first second) with (metal work conduct\$3))

L4: (504) 3 and (oxide 'TiN' titanium tantalum'Pt' 'Al' 'TaN')

L5: (474) 4 and (thick thickness)

L6: (123) 5 and ((thick thickness) with work adj function)

L7: (69) 6 and (transistor gate)

L8: (69) 7 and work adj function

Search

DBs: ☐ USPAT; ☐ US-PGPUB; ☐ EPO; ☐ JPO; ☐ DERWENT; ☐ ☒ Plurals

Default operator: ☒ Highlight all hit terms initially

	U	1	Document ID	Issue Date	Pages	Title	Current OR	Current XRef
1	<input type="checkbox"/>	<input type="checkbox"/>	US 20020098377 A1	20020725	18	High resistance polyaniline useful in high efficiency pixellated polymer ele	428/690	252/500;
2	<input type="checkbox"/>	<input type="checkbox"/>	US 20020089477 A1	20020711	22	Display apparatus, display apparatus driving method, and liquid crystal dis	345/87	257/40;
3	<input type="checkbox"/>	<input type="checkbox"/>	US 20020061646 A1	20020523	13	Embedded metal nanocrystals	438/660	
4	<input type="checkbox"/>	<input type="checkbox"/>	US 20020057050 A1	20020516	87	Organic light emitting diode devices using aromatic amine compounds wit	313/504	430/58.15;
5	<input type="checkbox"/>	<input type="checkbox"/>	US 20020055319 A1	20020509	31	Low gate current field emitter cell and array with vertical thin-film-edge emitt	445/24	430/58.5;
6	<input type="checkbox"/>	<input type="checkbox"/>	US 20020042241 A1	20020411	32	Low gate current field emitter cell and array with vertical thin-film-edge emitt	445/24	
7	<input type="checkbox"/>	<input type="checkbox"/>	US 20020039730 A1	20020404	10	Organic electroluminescent device and manufacturing method therefor	435/6	
8	<input type="checkbox"/>	<input type="checkbox"/>	US 20020036291 A1	20020328	21	Multilayer structures as stable hole-injecting electrodes for use in hig	257/72	
9	<input type="checkbox"/>	<input type="checkbox"/>	US 20020021088 A1	20020221	22	Organic light emitting diode devices with improved anode stability	313/504	313/506
10	<input type="checkbox"/>	<input type="checkbox"/>	US 20020021068 A1	20020221	9	E-M WAVE GENERATION USING COLD ELECTRON EMISSION	313/231.61	

Start

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10:22 AM